

# PBDTC124ET

50 V, 100 mA low VCEsat NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

9 October 2025

Product data sheet

## 1. General description

NPN low  $V_{CEsat}$  energy efficient Resistor-Equipped Transistor (RET) in a small SOT23 Surface-Mounted Device (SMD) plastic package.

PNP complement: PBDTA124ET

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current gain (h<sub>FE</sub>)
- · High energy efficiency due to less heat generation
- Improved device reliability due to reduced heat generation
- Built-in bias resistors
- Reduces component count
- Reduces pick and place costs
- · Simplifies circuit design

## 3. Applications

- · Digital applications in industrial segments
- · Battery-driven low power devices
- Load-switches
- Low current drivers
- · Power management and charging circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base		-	-	50	V
Io	output current			-	-	100	mA
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	[1]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[1]	0.8	1	1.2	

[1] See "Section 11: Test information" for resistor calculation and test conditions.



50 V, 100 mA low VCEsat NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)	]3	
2	GND	ground (emitter)		R1
3	0	output (collector)	SOT23	GND R2 sym007

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package	Package					
	Name	Description	Version				
PBDTC124ET	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23				

# 7. Marking

### Table 4. Marking codes

Type number	Marking code[1]
PBDTC124ET	%6P

[1] % = placeholder for manufacturing site code

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50 V, 100 mA low VCEsat NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

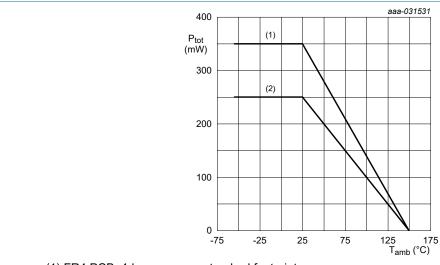
# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	10	V
VI	input voltage			-10	60	V
I <sub>O</sub>	output current			-	100	mA
I <sub>OM</sub>	peak output current	single pulse; t <sub>p</sub> ≤ 1 ms		-	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	250	mW
			[2]	-	350	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.



- (1) FR4 PCB, 4-layer copper, standard footprint
- (2) FR4 PCB, single-sided copper, tin-plated and standard footprint

Fig. 1. Power derating curves

50 V, 100 mA low VCEsat NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

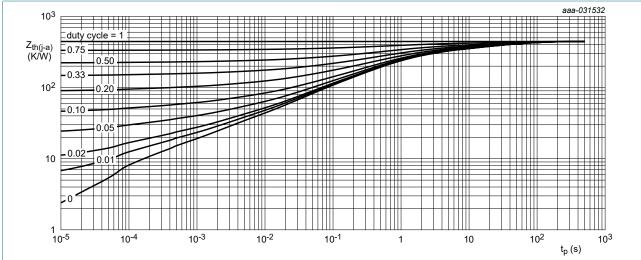
### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

 $T_{amb}$  = 25 °C unless otherwise specified.

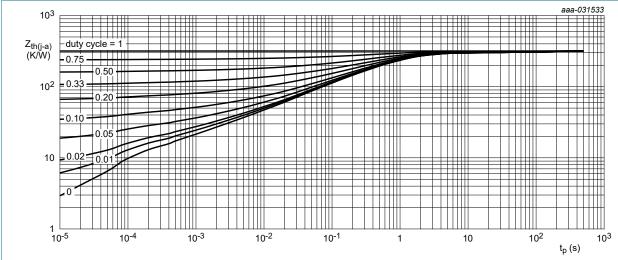
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	-	500	K/W
junction to ambient		[2]	-	-	357	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	130	K/W

- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.



FR4 PCB, single-sided copper, tin-plated and standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer copper, tin-plated and standard footprint.

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

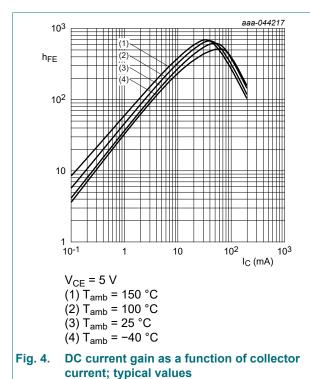
50 V, 100 mA low VCEsat NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		50	-	-	V
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
	current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	5	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	180	μΑ
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C		145	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	100	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C		-	1.1	0.8	V
V <sub>I(on)</sub>	on-state input voltage	V <sub>CE</sub> = 0.3 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C		3	2.3	-	V
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	[1]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[1]	8.0	1	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	-	2	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[2]	-	245	-	MHz

- [1] See "Section 11: Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor.



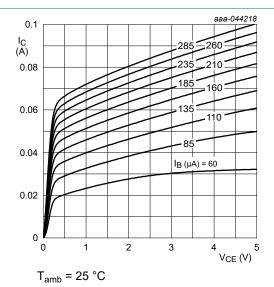
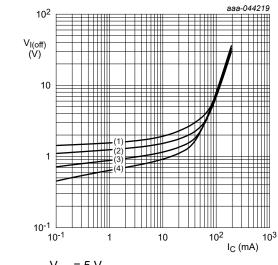


Fig. 5. Collector current as a function of collectoremitter voltage; typical values

#### 50 V, 100 mA low VCEsat NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

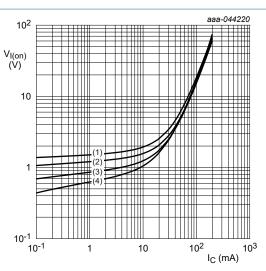


 $V_{CE}$  = 5 V (1)  $T_{amb}$  = -40 °C

(2)  $T_{amb}$  = 25 °C

(3) T<sub>amb</sub> = 100 °C (4) T<sub>amb</sub> = 150 °C



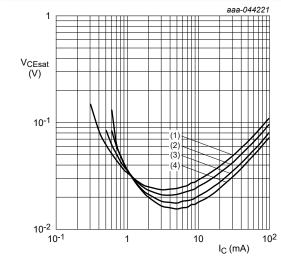


 $V_{CE} = 0.3 V$ (1)  $T_{amb} = -40 \,^{\circ}C$ 

(2)  $T_{amb}$  = 25 °C

(3) T<sub>amb</sub> = 100 °C (4) T<sub>amb</sub> = 150 °C

Off-state input voltage as a function of collector | Fig. 7. On-state input voltage as a function of collector current; typical values



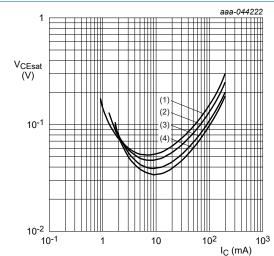
 $I_C/I_B = 20$ 

 $(1) T_{amb} = 150 °C$ 

(2)  $T_{amb} = 100 \, ^{\circ}C$ 

(3) T<sub>amb</sub> = 25 °C (4) T<sub>amb</sub> = -40 °C

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_C/I_B = 50$ (1)  $T_{amb} = 150 \, ^{\circ}C$ 

(2)  $T_{amb} = 100 \, ^{\circ}C$ 

(3)  $T_{amb} = 25 \, ^{\circ}C$ 

(4)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

### 50 V, 100 mA low VCEsat NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

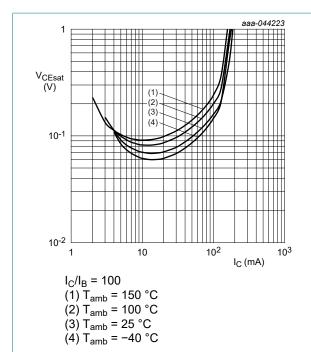


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

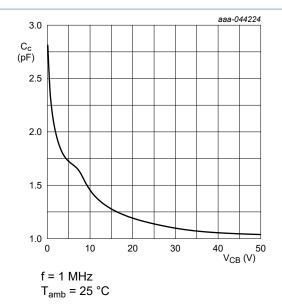


Fig. 11. Collector capacitance as a function of collectorbase voltage; typical values

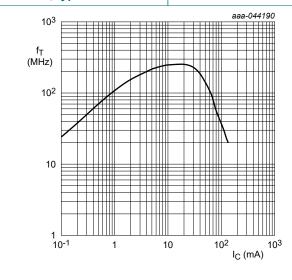


Fig. 12. Transition frequency as a function of collector current; typical values of built-in transistor

f = 100 MHz  $V_{CE} = 5 \text{ V}$  $T_{amb} = 25 \text{ °C}$ 

50 V, 100 mA low VCEsat NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

## 11. Test information

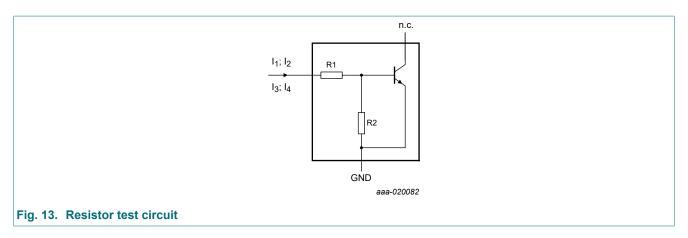
#### **Resistor calculation**

· Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{1})}{I_{2} - I_{1}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

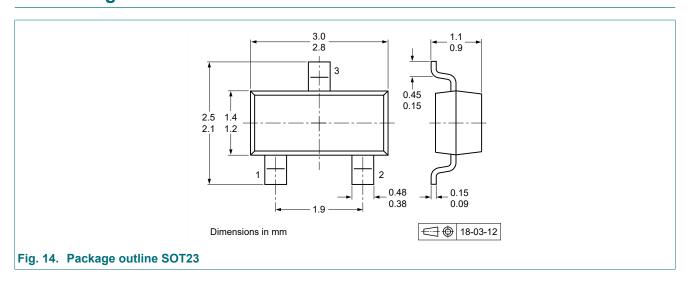


### **Resistor test conditions**

**Table 8. Resistor test conditions** 

Type number	R1 (kΩ)	R2 (kΩ)	Test conditions	S		
			I <sub>1</sub>	l <sub>2</sub>	l <sub>3</sub>	14
PBDTC124ET	22	22	550 μΑ	750 µA	-150 μA	-230 µA

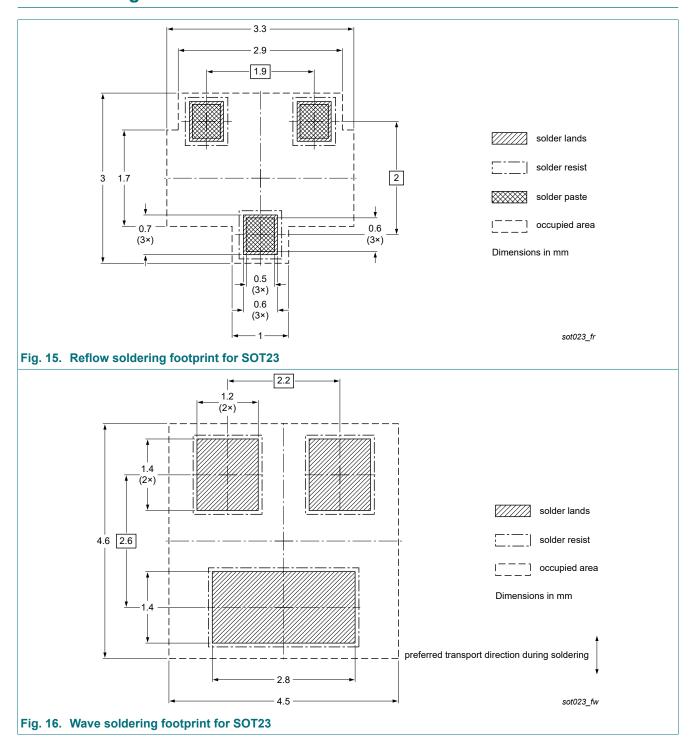
# 12. Package outline



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50 V, 100 mA low VCEsat NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

# 13. Soldering



50 V, 100 mA low VCEsat NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

# 14. Revision history

#### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBDTC124ET v.1	20251009	Product data sheet	-	-		

#### 50 V, 100 mA low VCEsat NPN resistor-equipped transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- 2] The term 'short data sheet' is explained in section "Definitions".
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